

# Thyristor/Thyristor, 150 A (New INT-A-PAK Power Module)



**New INT-A-PAK** 

PRODUCT SUMMARY						
I <sub>T(AV)</sub>	150 A					
Туре	Modules - Thyristor, Standard					
Package	INT-A-PAK					
Circuit	Two SCRs doubler circuit					

#### **FEATURES**

• Electrically isolated by DBC ceramic (Al<sub>2</sub>O<sub>3</sub>)



- 3500 V<sub>RMS</sub> isolating voltage
- Industrial standard package
- High surge capability
- Glass passivated chips
- Simple mounting
- UL approved file E78996
- · Designed and qualified for multiple level
- Material categorization: For definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **APPLICATIONS**

- · Battery charges
- Welders
- Power converters

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
I <sub>T(AV)</sub>	85 °C	150	Α					
I <sub>T(RMS)</sub>		330						
1	50 Hz	4000	Α					
I <sub>TSM</sub>	60 Hz	4200						
l <sup>2</sup> t	50 Hz	80	kA <sup>2</sup> s					
I-(	60 Hz	73	KA-S					
I <sup>2</sup> √t		800	kA <sup>2</sup> √s					
V <sub>RRM</sub>		400	V					
T <sub>Stg</sub>	Range	-40 to 150	°C					
$T_J$	Range	-40 to 125						

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> /V <sub>DSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-VSKT152/04PbF	400	500	50					



ON-STATE CONDUCTION						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	180° conductio	on half sine wave		150	А
at case temperature	T(AV)	100 conduction	on nan one wave		85	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	As AC switch			330	
		t = 10 ms	No voltage		4000	
Maximum peak, one-cycle	١.	t = 8.3 ms	reapplied		4200	Α
on-state, non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		3350	
		t = 8.3 ms	= 8.3 ms reapplied Sine half w		3500	
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	80	kA <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	t = 8.3 ms reapplied	reapplied		73	
waximum in for fusing	1-1	t = 10 ms	100 % V <sub>RRM</sub>		56	
		t = 8.3 ms	reapplied		51	
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 1	0 ms, no voltage i	reapplied	800	kA <sup>2√</sup> s
Value of threshold voltage	V <sub>T(TO)</sub>	T			0.82	V
On-state slope resistance	r <sub>t</sub>	T <sub>J</sub> maximum		1.44	mΩ	
Maximum on-state voltage drop	V <sub>TM</sub>	$I_{pk} = \pi \times I_{T(AV)}, T_J = 25  ^{\circ}C$			1.48	V
Maximum holding current	I <sub>H</sub>	T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load, gate open circuit			200	mA
Maximum latching current	ΙL	$T_J = 25  ^{\circ}C$ , and	ode supply = 6 V,	resistive load	400	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Typical delay time	t <sub>gd</sub>	T <sub>.1</sub> = 25 °C	Gate current = 1 A, dl <sub>g</sub> /dt = 1 A/µs V <sub>d</sub> = 0.67 % V <sub>DRM</sub>	1	
Typical rise time	t <sub>gr</sub>	11 = 25 0	$V_{d} = 0.67 \% V_{DRM}$	2	μs
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 300 A, - dl/dt = 15 A/μs; $T_J$ = $T_J$ maximum $V_R$ = 50 V; dV/dt = 20 V/μs; gate 0 V, 100 $\Omega$		50 to 200	

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak reverse and off-state leakage current	I <sub>RRM,</sub> I <sub>DRM</sub>	T <sub>J</sub> = 125 °C	50	mA			
RMS insulation voltage	V <sub>INS</sub>	50 Hz, circuit to base, all terminals shorted, t = 1 s	3500	V			
Critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, exponential to 67 % rated $V_{DRM}$	1000	V/µs			



TRIGGERING						
PARAMETER	SYMBOL	TEST CON	IDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$t_p \le 5 \text{ ms}, T_J = T_J \text{ maxim}$	num	12	w	
Maximum average gate power	P <sub>G(AV)</sub>	$f = 50 \text{ Hz}, T_J = T_J \text{ maxim}$	num	3	VV	
Maximum peak gate current	I <sub>GM</sub>			3	Α	
Maximum peak negative gate voltage	- V <sub>GT</sub>	$t_p \le 5$ ms, $T_J = T_J$ maxim	num	10		
		T <sub>J</sub> = - 40 °C		4	V	
Maximum required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C		2.5		
		$T_J = T_J$ maximum Anode supply = 6 V,		1.7		
		$T_J = -40  ^{\circ}\text{C}$ resistive load; $R_a = 1  \Omega$	$T_J = -40  ^{\circ}\text{C}$ resistive load; $R_a = 1  \Omega$			
Maximum required DC gate current to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		150	mA	
our one to ungger		$T_J = T_J$ maximum		80		
Maximum gate voltage that will not trigger	$V_{GD}$	T <sub>J</sub> = T <sub>J</sub> maximum, rated	V applied	0.3	V	
Maximum gate current that will not trigger	I <sub>GD</sub>	rj – rjinaximum, fated	VDRM applied	10	mA	
Maximum rate of rise of turned-on current	dl/dt	$T_J = T_J$ maximum, $I_{TM} = 4$	400 A rated V <sub>DRM</sub> applied	300	A/μs	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction temperature range		TJ		- 40 to 125	°C		
Maximum storage temperature range		T <sub>Stg</sub>		- 40 to 150	O		
Maximum thermal junction to case pe	,	R <sub>thJC</sub>	DC operation	0.18	K/W		
Maximum thermal resistance, case to heatsink per module		R <sub>thCS</sub>	Mounting surface smooth, flat and greased 0.05		T IV VV		
Mounting	IAP to heatsink		A	4 to 6	Nm		
torque ± 10 %	busbar to IAP		A mounting compound is recommended and the torque should be rechecked after a period of	4 10 6	INIII		
Ammavimatawaia	h.t		3 hours to allow for the spread of the compound. Lubricated threads.	200	g		
Approximate weig	III		Lubilicated till cads.	7.1	oz.		
Case style				INT-A-	PAK		

△R CONDUCTION PER JUNCTION											
SINUSOIDAL CONDUCTION RECTANGULAR CONDUCTION AT T <sub>J</sub> MAXIMUM AT T <sub>J</sub> MAXIMUM								UNITS			
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSKT152/04PbF	0.007	0.010	0.013	0.016	0.017	0.009	0.012	0.014	0.016	0.017	K/W

#### Note

• Table shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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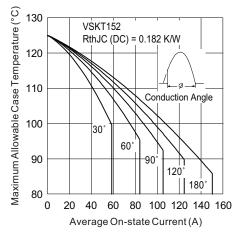


Fig. 1 - Current Ratings Characteristics

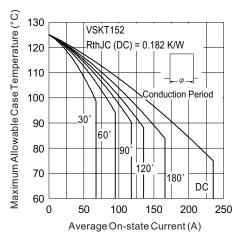


Fig. 2 - Current Ratings Characteristics

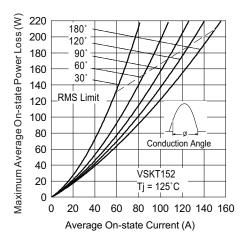


Fig. 3 - Forward Power Loss Characteristics

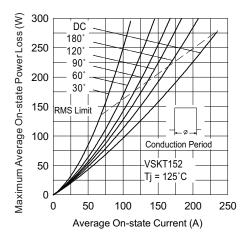


Fig. 4 - Forward Power Loss Characteristics

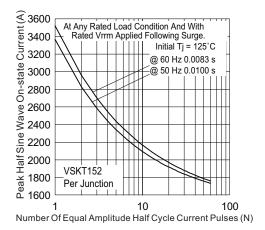


Fig. 5 - Maximum Non-Repetitive Surge Current

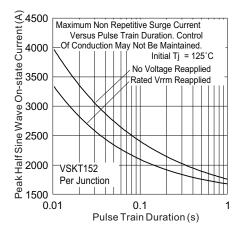


Fig. 6 - Maximum Non-Repetitive Surge Current

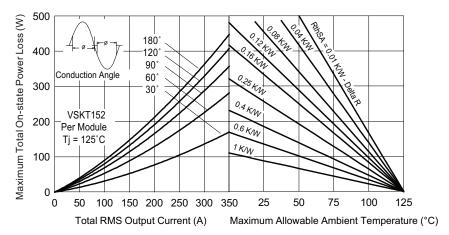


Fig. 7 - On-State Power Loss Characteristics

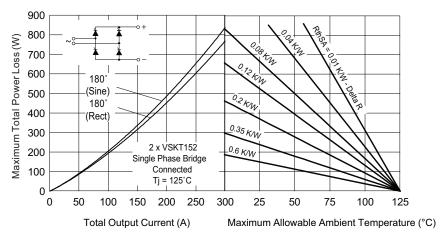


Fig. 8 - On-State Power Loss Characteristics

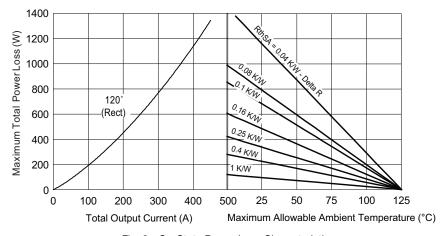


Fig. 9 - On-State Power Loss Characteristics



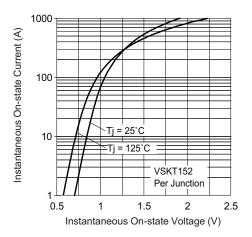


Fig. 10 - On-State Voltage Drop Characteristics

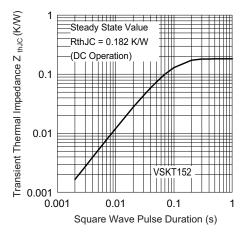


Fig. 11 - Thermal Impedance Z<sub>thJC</sub> Characteristics

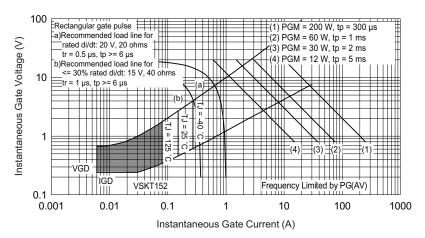
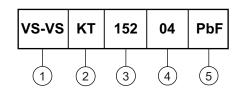


Fig. 12 - Gate Characteristics



#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Circuit configuration

Current rating

4 - Voltage rating (04 = 400 V)

5 - PbF = Lead (Pb)-free

#### Note

• To order the optional hardware go to <a href="https://www.vishay.com/doc?95172">www.vishay.com/doc?95172</a>

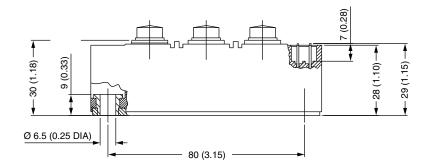
CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs doubler circuit	Т	10~ 10~ 20+ NO 100 100 100 100 100 100 100 100 100 10

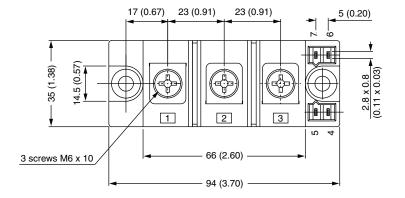
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95067			

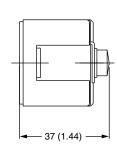


# **INT-A-PAK IGBT/Thyristor**

#### **DIMENSIONS** in millimeters (inches)









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Revision: 02-Oct-12 Document Number: 91000

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